

### Features

- ☐ High-speed access times  
Com'l: 70, 85 and 100ns
- ☐ Low power operation (typical)
  - PDM31096LL
  - Active: 65 mW
  - Standby: 10μW
- ☐ Single +3.3V (±0.3V) power supply
- ☐ TTL-compatible inputs and outputs
- ☐ I/Os are 5V tolerant
- ☐ Low data retention voltage: 1.5V
- ☐ Packages
  - Plastic TSOP (I) - T
  - Plastic STSOP (I) - ST

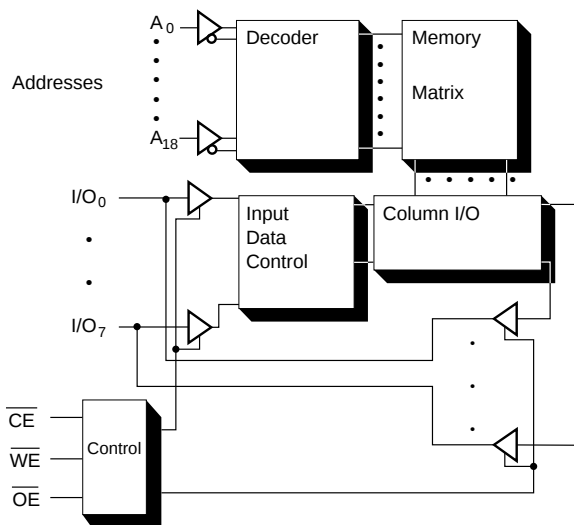
### Description

The PDM31096LL is a very low power CMOS static RAM organized as 524,288 x 8 bits. Writing to this device is accomplished when the write enable ( $\overline{WE}$ ) and the chip enable ( $\overline{CE}$ ) inputs are both LOW. Reading is accomplished when  $\overline{WE}$  remains HIGH and  $\overline{CE}$  and  $\overline{OE}$  are both LOW.

The PDM31096LL operates from a single +3.3V power supply and all the inputs and outputs are fully TTL- compatible. The device supports low data retention voltage for battery back-up operation with low current.

The PDM31096LL is available in a 32-pin plastic TSOP (I) and a 32-pin plastic STSOP (I).

### Functional Block Diagram



## Pin Configurations

## TSOP (I), STSOP (I)

|                        |    |    |                        |
|------------------------|----|----|------------------------|
| A11                    | 1  | 32 | $\overline{\text{OE}}$ |
| A9                     | 2  | 31 | A10                    |
| A8                     | 3  | 30 | $\overline{\text{CE}}$ |
| A13                    | 4  | 29 | I/O7                   |
| $\overline{\text{WE}}$ | 5  | 28 | I/O6                   |
| A17                    | 6  | 27 | I/O5                   |
| A15                    | 7  | 26 | I/O4                   |
| V <sub>CC</sub>        | 8  | 25 | I/O3                   |
| A18                    | 9  | 24 | V <sub>SS</sub>        |
| A16                    | 10 | 23 | I/O2                   |
| A14                    | 11 | 22 | I/O1                   |
| A12                    | 12 | 21 | I/O0                   |
| A7                     | 13 | 20 | A0                     |
| A6                     | 14 | 19 | A1                     |
| A5                     | 15 | 18 | A2                     |
| A4                     | 16 | 17 | A3                     |

## Pin Description

| Name                   | Description         |
|------------------------|---------------------|
| A18-A0                 | Address Inputs      |
| I/O7-I/O0              | Data Inputs/Outputs |
| $\overline{\text{OE}}$ | Output Enable Input |
| $\overline{\text{WE}}$ | Write Enable Input  |
| $\overline{\text{CE}}$ | Chip Enable Input   |
| V <sub>CC</sub>        | Power (+3.3V)       |
| V <sub>SS</sub>        | Ground              |

## Truth Table

| $\overline{\text{OE}}$ | $\overline{\text{WE}}$ | $\overline{\text{CE}}$ | I/O              | MODE           |
|------------------------|------------------------|------------------------|------------------|----------------|
| X                      | X                      | H                      | Hi-Z             | Standby        |
| X                      | X                      | X                      | Hi-Z             | Standby        |
| L                      | H                      | L                      | D <sub>OUT</sub> | Read           |
| X                      | L                      | L                      | D <sub>IN</sub>  | Write          |
| H                      | H                      | L                      | Hi-Z             | Output Disable |

NOTE: H = V<sub>IH</sub>, L = V<sub>IL</sub>, X = DON'T CARE

Absolute Maximum Ratings <sup>(1)</sup>

| Symbol            | Rating                                           | Com'l.       | Ind.         | Unit |
|-------------------|--------------------------------------------------|--------------|--------------|------|
| V <sub>TERM</sub> | Terminal Voltage with Respect to V <sub>SS</sub> | -0.5 to +4.6 | -0.5 to +4.6 | V    |
| T <sub>BIAS</sub> | Temperature Under Bias                           | -55 to +125  | -65 to +135  | °C   |
| T <sub>STG</sub>  | Storage Temperature                              | -55 to +125  | -65 to +150  | °C   |
| P <sub>T</sub>    | Power Dissipation                                | 1.0          | 1.0          | W    |
| I <sub>OUT</sub>  | DC Output Current                                | 20           | 20           | mA   |
| T <sub>j</sub>    | Maximum Junction Temperature <sup>(2)</sup>      | 125          | 125          | °C   |

- NOTE: 1. Stresses greater than those listed under ABSOLUTE MAXIMUM RATINGS may cause permanent damage to the device. This is a stress rating only and functional operation of the device at these or any other conditions above those indicated in the operational sections of this specification is not implied. Exposure to absolute maximum rating conditions for extended periods may affect reliability.
2. Appropriate thermal calculations should be performed in all cases and specifically for those where the chosen package has a large thermal resistance (e.g., TSOP). The calculation should be of the form:  $T_j = T_a + P * \theta_{ja}$  where  $T_a$  is the ambient temperature, P is average operating power and  $\theta_{ja}$  the thermal resistance of the package. For this product, use the following  $\theta_{ja}$  values:

SOJ: 78 °C/W  
TSOP: 112 °C/W

**Recommended DC Operating Conditions**

| Symbol          | Parameter           | Min. | Typ. | Max. | Unit |
|-----------------|---------------------|------|------|------|------|
| V <sub>CC</sub> | Supply Voltage      | 3.0  | 3.3  | 3.6  | V    |
| V <sub>SS</sub> | Supply Voltage      | 0    | 0    | 0    | V    |
| Commercial      | Ambient Temperature | 0    | 25   | 70   | °C   |

**DC Electrical Characteristics** (V<sub>CC</sub> = 3.3V ± 0.3V)

| Symbol           | Parameter                         | Test Conditions                                                                                             | Min.                | Typ. <sup>(2)</sup> | Max.                 | Unit |
|------------------|-----------------------------------|-------------------------------------------------------------------------------------------------------------|---------------------|---------------------|----------------------|------|
| I <sub>LI</sub>  | Input Leakage Current             | V <sub>CC</sub> = MAX., V <sub>IN</sub><br>= V <sub>SS</sub> to V <sub>CC</sub>                             | -1                  | —                   | 1                    | μA   |
| I <sub>LO</sub>  | Output Leakage Current            | V <sub>CC</sub> = MAX.,<br>CE = V <sub>IH</sub><br>V <sub>OUT</sub> = V <sub>SS</sub> to<br>V <sub>CC</sub> | -1                  | —                   | 1                    | μA   |
| V <sub>IL</sub>  | Input Low Voltage                 |                                                                                                             | -0.3 <sup>(1)</sup> | —                   | 0.8                  | V    |
| V <sub>IH</sub>  | Input High Voltage                |                                                                                                             | 2.2                 | —                   | V <sub>CC</sub> +0.3 | V    |
| V <sub>OL</sub>  | Output Low Voltage                | I <sub>OL</sub> = 2mA, V <sub>CC</sub><br>= Min.                                                            | —                   | —                   | 0.4                  | V    |
| V <sub>OH</sub>  | Output High Voltage               | I <sub>OH</sub> = -1 mA,<br>V <sub>CC</sub> = Min.                                                          | 2.4                 | —                   | —                    | V    |
| I <sub>CC</sub>  | Operating Power Supply<br>Current | V <sub>CC</sub> = MAX<br>CE = V <sub>IL</sub><br>I <sub>OUT</sub> = 0 mA<br>f = f <sub>MAX</sub>            | —                   | —                   | 40                   | mA   |
| I <sub>SB</sub>  | Standby Current (TTL)             | V <sub>CC</sub> = MAX<br>CE = V <sub>IH</sub>                                                               | —                   | —                   | 1                    | mA   |
| I <sub>SB1</sub> | Full Standby Current<br>(CMOS)    | V <sub>CC</sub> = MAX<br>CE ≥ V <sub>CC</sub> -0.2V<br>V <sub>IN</sub> ≥ V <sub>CC</sub> -0.2V<br>or ≤ 0.2V | —                   | 3 μA                | 60                   | μA   |

NOTE:1. V<sub>IL</sub>(min) = -3.0V for pulse width less than 20 ns. 2. V<sub>CC</sub> = 3.3V, 25C.

**Data Retention Characteristics**

| Symbol       | Parameter                            | Test Conditions                                                                     | Min.     | Typ. <sup>(1)</sup> | Max. | Unit    |
|--------------|--------------------------------------|-------------------------------------------------------------------------------------|----------|---------------------|------|---------|
| $V_{DR}$     | $V_{CC}$ for data retention          | $\overline{CE} \geq V_{CC} - 0.2V$<br>$V_{IN} \geq V_{CC} - 0.2V$<br>or $\leq 0.2V$ | 1.5      | —                   | —    | V       |
| $I_{CC\ DR}$ | Data retention current               | $\overline{CE} \geq V_{CC} - 0.2V$<br>$V_{IN} \geq V_{CC} - 0.2V$<br>or $\leq 0.2V$ | —        | 1.5                 | 40   | $\mu A$ |
| $t_{CDR}$    | Chip deselect to data retention time | See waveform                                                                        | 0        | —                   | —    | ns      |
| $t_R$        | Recovery time                        | See waveform                                                                        | $t_{RC}$ | —                   | —    | ns      |

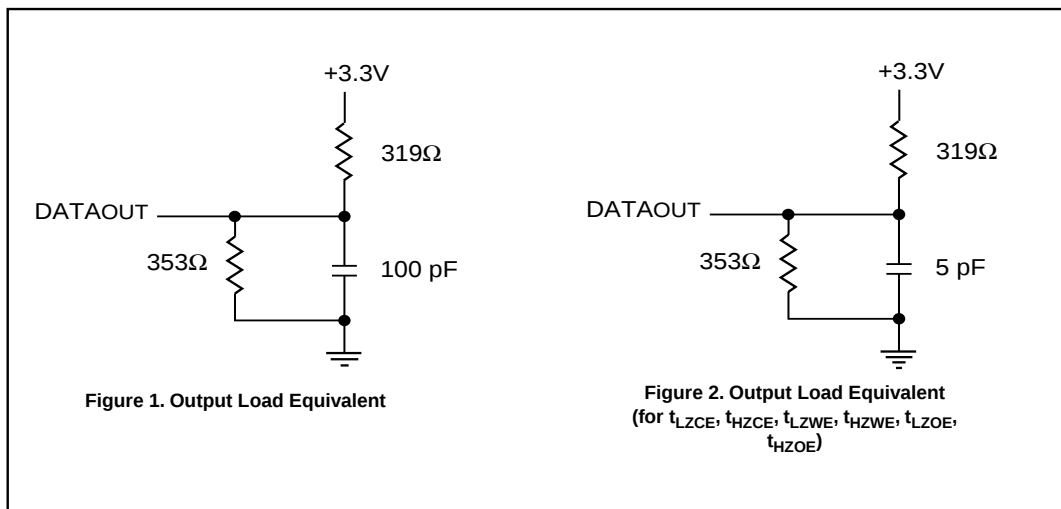
NOTE: 1.  $V_{CC} = 3.3V$ , 25C.**Capacitance<sup>(1)</sup>** ( $T_A = +25^\circ C$ ,  $f = 1.0\ MHz$ )

| Symbol    | Parameter          | Max. | Unit |
|-----------|--------------------|------|------|
| $C_{IN}$  | Input Capacitance  | 6    | pF   |
| $C_{OUT}$ | Output Capacitance | 8    | pF   |

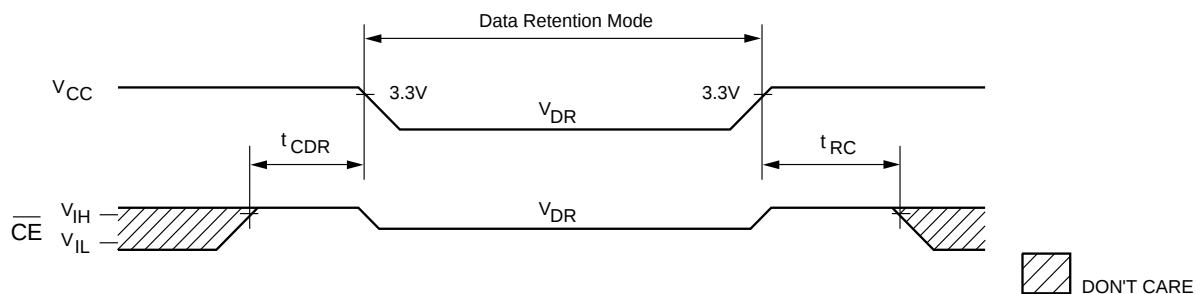
NOTE: 1. This parameter is determined by device characterization but is not production tested.

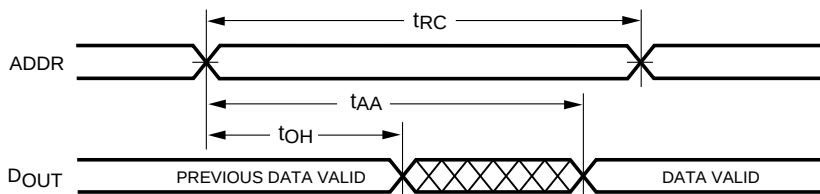
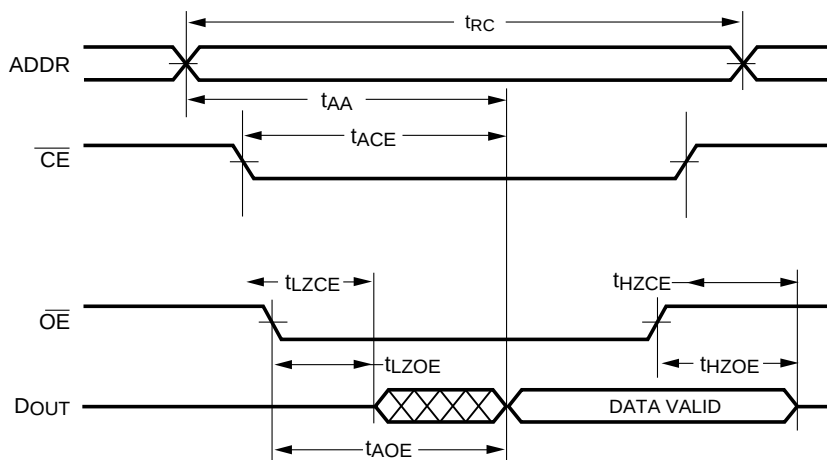
**AC Test Conditions**

|                               |                     |
|-------------------------------|---------------------|
| Input pulse levels            | $V_{SS}$ to 3.0V    |
| Input rise and fall times     | 5 ns                |
| Input timing reference levels | 1.5V                |
| Output reference levels       | 1.5V                |
| Output load                   | See Figures 1 and 2 |



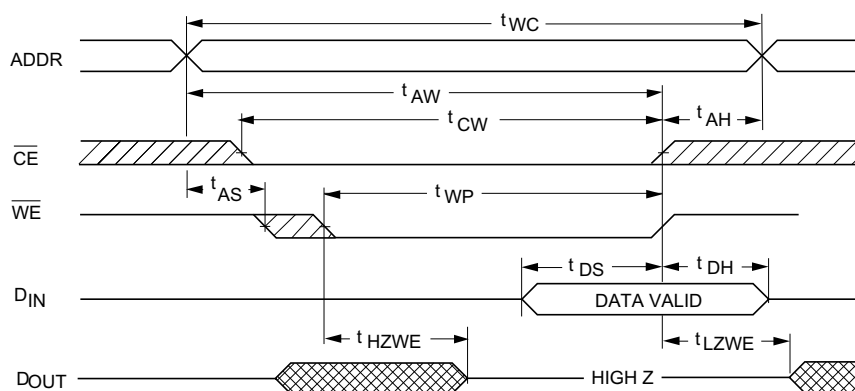
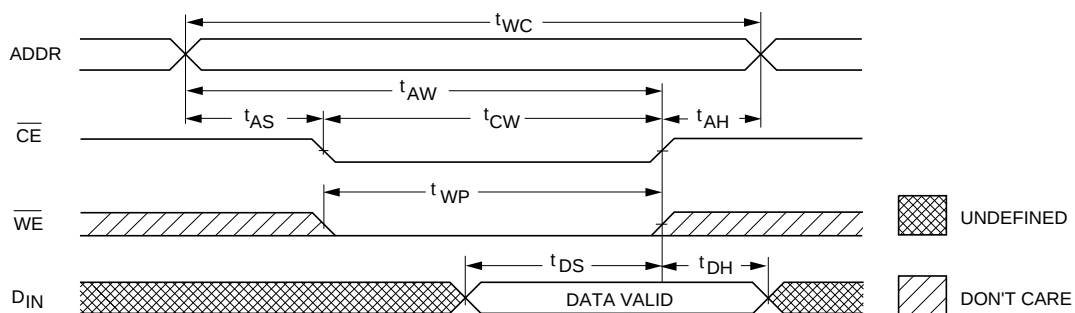
### Low $V_{CC}$ Data Retention Waveform



Read Cycle No. 1<sup>(1)</sup>Read Cycle No. 2<sup>(2)</sup>

## AC Electrical Characteristics

| Description                                  |            | -70  |      | -85  |      | -100 |     |       |
|----------------------------------------------|------------|------|------|------|------|------|-----|-------|
| READ Cycle                                   | Sym        | Min. | Max. | Min. | Max. | Min  | Max | Units |
| READ cycle time                              | $t_{RC}$   | 70   |      | 85   |      | 100  |     | ns    |
| Address access time                          | $t_{AA}$   |      | 70   |      | 85   |      | 100 | ns    |
| Chip enable access time                      | $t_{ACE}$  |      | 70   |      | 85   |      | 100 | ns    |
| Output hold from address change              | $t_{OH}$   | 10   |      | 10   |      | 10   |     | ns    |
| Chip enable to output in low $Z^{(3,4,5)}$   | $t_{LZCE}$ | 10   |      | 10   |      | 10   |     | ns    |
| Chip disable to output in high $Z^{(3,4,5)}$ | $t_{HZCE}$ |      | 35   |      | 35   |      | 35  | ns    |
| Output enable access time                    | $t_{AOE}$  |      | 50   |      | 50   |      | 50  | ns    |
| Output enable to output in low $Z^{(4,5)}$   | $t_{LZOE}$ | 10   |      | 10   |      | 10   |     | ns    |
| Output disable to output in high $Z^{(4,5)}$ | $t_{HZOE}$ |      | 30   |      | 30   |      | 30  | ns    |

**Write Cycle No. 1 (Write Enable Controlled)****Write Cycle No. 2 (Chip Enable Controlled)**

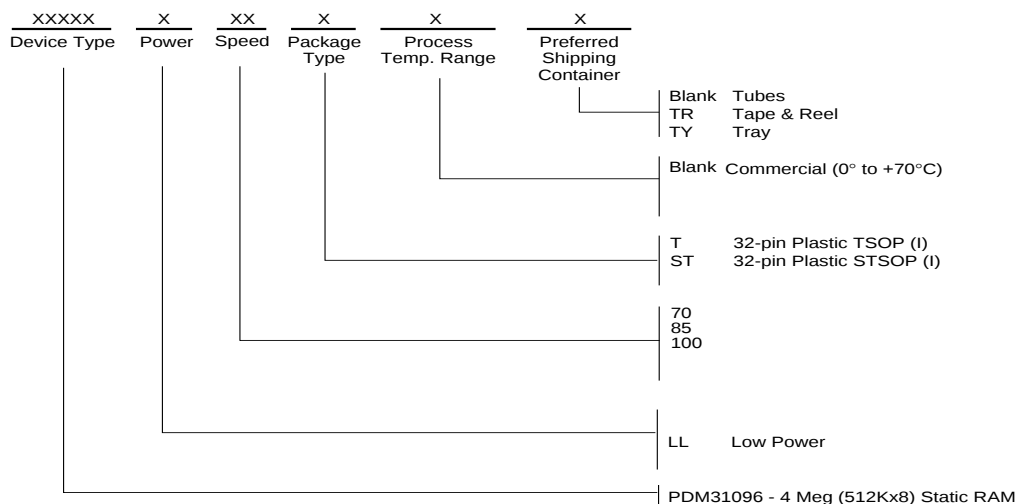
## AC Electrical Characteristics

| Description                                |            | -70  |      | -85  |      | -100 |      |       |
|--------------------------------------------|------------|------|------|------|------|------|------|-------|
| WRITE Cycle                                | Sym        | Min. | Max. | Min. | Max. | Min. | Max. | Units |
| WRITE cycle time                           | $t_{WC}$   | 70   |      | 85   |      | 100  |      | ns    |
| Chip enable to end of write                | $t_{CW}$   | 70   |      | 85   |      | 100  |      | ns    |
| Address valid to end of write              | $t_{AW}$   | 70   |      | 85   |      | 100  |      | ns    |
| Address setup time                         | $t_{AS}$   | 0    |      | 0    |      | 0    |      | ns    |
| Address hold from end of write             | $t_{AH}$   | 0    |      | 0    |      | 0    |      | ns    |
| Write pulse width                          | $t_{WP}$   | 50   |      | 50   |      | 50   |      | ns    |
| Data setup time                            | $t_{DS}$   | 40   |      | 40   |      | 40   |      | ns    |
| Data hold time                             | $t_{DH}$   | 0    |      | 0    |      | 0    |      | ns    |
| Write disable to output in low $Z^{(4,5)}$ | $t_{LZWE}$ | 5    |      | 5    |      | 5    |      | ns    |
| Write enable to output in high $Z^{(4,5)}$ | $t_{HZWE}$ |      | 30   |      | 30   |      | 30   | ns    |

NOTES: (For two previous Electrical Characteristics tables)

1. The device is continuously selected. Chip Enable is held in its active state.
2. The address is valid prior to or coincident with the latest occurring Chip Enable.
3. At any given temperature and voltage condition,  $t_{HZCE}$  is less than  $t_{LZCE}$ .
4. This parameter is sampled.
5. The parameter is tested with  $CL = 5$  pF as shown in Figure 2. Transition is measured  $\pm 500$  mV from steady state voltage.

## Ordering Information



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